

## isc Silicon PNP Power Transistor

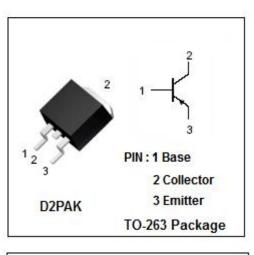
# MJB45H11

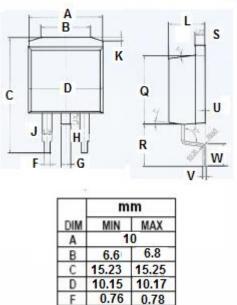
#### DESCRIPTION

- Low Collector-Emitter saturation voltage
- Pb-free package are available
- Fast switching speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

 General purpose amplification and switching such as out or driver stages in applications such as switching regulators,converters and power amplifiers





1.26

1.6

0.6

4.8

8.71

5.30

1.28

0.2

0.39

2.82

1.4

1.33

0.4

4.6

8.69

5.28

1.26

0.0

0.37

2.80

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CEO</sub>	Collector-Emitter Voltage	-80	V
VEBO	Emitter-Base Voltage	-5	V
lc	Collector Current-Continuous	-10	А
I <sub>CP</sub>	Collector Current-Pulse	-20	A
Pc	Total Power Dissipation @ Ta=25℃	2	W
Pc	Total Power Dissipation @ Tc=25℃	50	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

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### isc website: <u>www.iscsemi.com</u>



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## **ELECTRICAL CHARACTERISTICS**

### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	lc=- 30mA; l <sub>B</sub> = 0	-80			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =-8A; I <sub>B</sub> =- 400mA			-1.0	V
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	I <sub>C</sub> =-8A; I <sub>B</sub> = -800mA			-1.5	V
Iceo	Collector Cutoff Current	V <sub>CE</sub> = -80V; I <sub>E</sub> = 0			-10	uA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-50	uA
$h_{\text{FE1}}$	DC Current Gain	I <sub>C</sub> = -2A; V <sub>CE</sub> =-1V	60			
h <sub>FE2</sub>	DC Current Gain	I <sub>C</sub> =-4A; V <sub>CE</sub> = -1V	40			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -10V		40		MHz
Сов	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = -10V; f= 1.0MHz		230		pF

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